

제22회 한국반도체학술대회

2015년 2월 10일(화) - 12일(목), 인천 송도컨벤시아

K. Memory (Design & Process Technology) 분과

Room E
1F / 108호

2015년 2월 12일(목) 13:10-14:40

[TE3-K] RRAM and FLASH Device, Modeling, and Process Technologies

좌장: 민경식 (국민대학교), 김수길 (SK Hynix Inc.)

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| TE3-K-1 | 14:50-15:05 | A Monte Carlo Simulation Model for an Anomalous ISPP Behavior in NAND Flash Memory
Jaeduk Lee, Youngwoo Park, Seong Soon Cho, Gyoyoung Jin, and Eunseung Jung
Semiconductor R&D Center, Samsung Electronics Co. Ltd. |
| TE3-K-2 | 15:05-15:20 | 3차원 플래시 메모리를 위한 채널 두께와 고체화 결정법에 의한 결정 크기 효과에 관한 연구
김승윤 ¹ , 박종경 ¹ , 이승준 ² , 이기홍 ² , 피승호 ² , 조병진 ¹
¹ 한국과학기술원전기 및 전자공학과, ² SK 하이닉스 반도체 메모리 연구소 |
| TE3-K-3 | 15:20-15:35 | Multi-State Resistance Controllability and Variability Analysis of Binary Oxide RRAM for Ultra-High Density Memory Applications
Amit Prakash, J-S. Park, J. Song, S-J. Lim, J-H. Park, J. Woo, E. Cha, and Hyunsang Hwang
Department of Materials Science and Engineering, Pohang University of Science and Technology |
| TE3-K-4 | 15:35-15:50 | Sub-Oxide Dependence of Insulator Metal Transition Characteristics on 3-D Structural Niobium Oxide Selector
Jaehyuk Park, Euijun Cha, Daeseok Lee, Jiyong Woo, Sangheon Lee, Jeonghwan Song, Jaesung Park, Yunmo Koo, and Hyunsang Hwang
Department of MS&E, POSTECH |
| TE3-K-5 | 15:50-16:05 | Improvement in Reliability Characteristics (Retention and Endurance) of RRAM by using High-Pressure Hydrogen Annealing
Jeonghwan Song, Daeseok Lee, Jiyong Woo, Euijun Cha, Sangheon Lee, and Hyunsang Hwang
Department of Materials Science and Engineering, Pohang University of Science and Technology |
| TE3-K-6 | 14:25-14:40 | Selector-less ReRAM with an Excellent Selectivity by the Tunnel Barrier Engineered Multi-Layer Titanium Oxide and Triangular Shaped AC Pulse
Sangheon Lee, Jiyong Woo, Jaesung Park, Jeonghwan Song, Daeseok Lee, and Hyunsang Hwang
Department of Materials Science and Engineering, POSTECH |